

Description

The AR3341P0S is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR3341P0S has a low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. The small size, low capacitance and high ESD surge protection make AR3341P0S an ideal choice to protect cell phone, digital visual interfaces, HDMI, DVI, USB2.0, USB3.0, and other high speed ports.

Features

- low capacitance: 0.6pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 14A (8/20 μs)
- RoHS Compliant

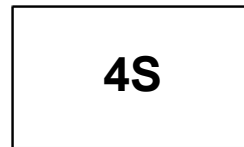
Mechanical Characteristics

- Package: DFN0603-2
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

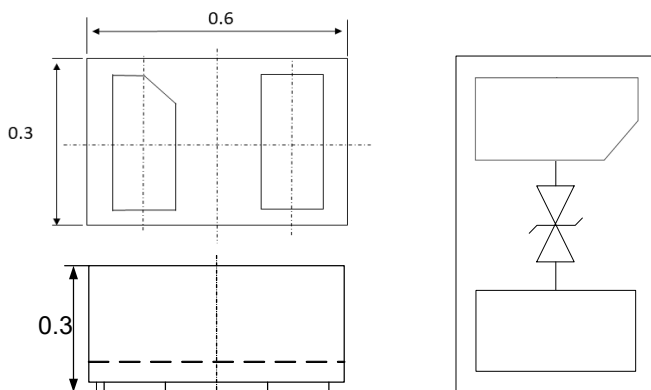
Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI / MHL
- USB 2.0 / USB 3.0
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



Dimensions and Pin Configuration



Package Dimensions

Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR3341P0S	10000/Tape & Reel	7 inch

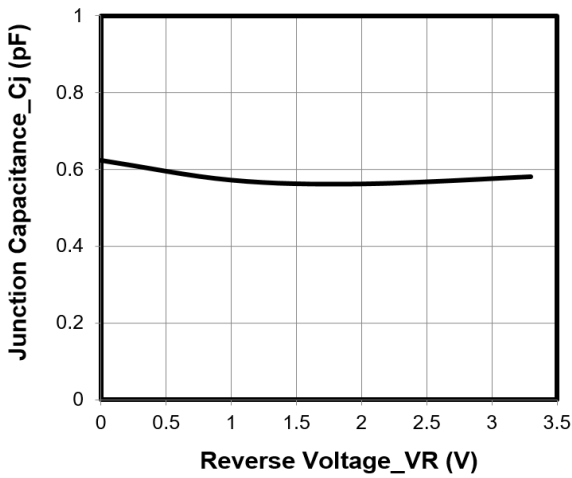
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	120	W
Peak Pulse Current (8/20μs)	I _{PP}	14	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±30 ±30	kV
Operating Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

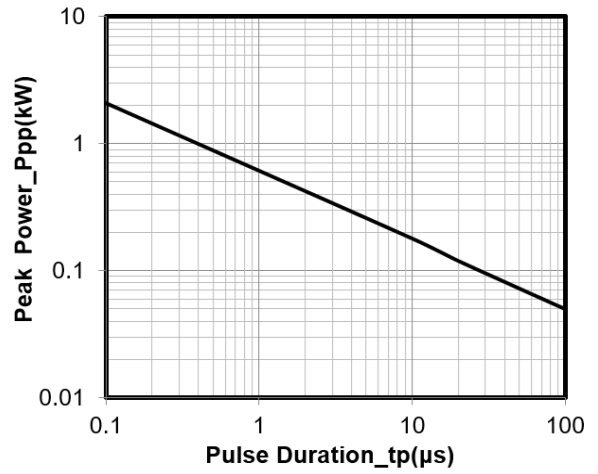
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Punch-Through Voltage	V _{PT}	3.5			V	I _{PT} = 2μA
Breakdown Voltage	V _{BR}	4			V	I _T = 1mA
Snap-Back Voltage	V _{SB}	2			V	I _{SB} = 50mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 3.3V
Clamping Voltage	V _C			8	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V _C			8	V	I _{PP} = 8A (8 x 20μs pulse)
Clamping Voltage	V _C			8.5	V	I _{PP} = 14A (8 x 20μs pulse)
Junction Capacitance	C _J		0.6		pF	V _R = 0V, f = 1MHz

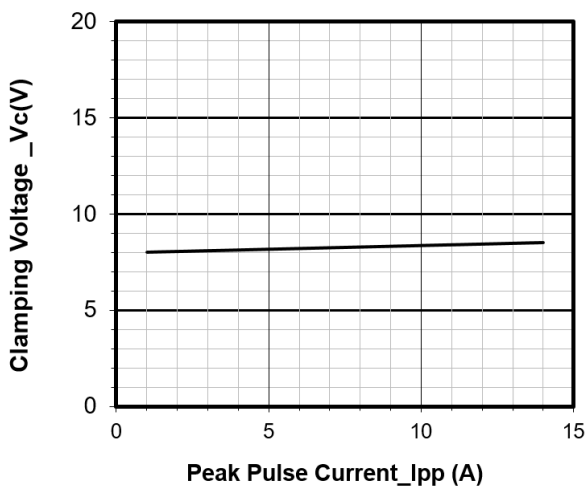
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



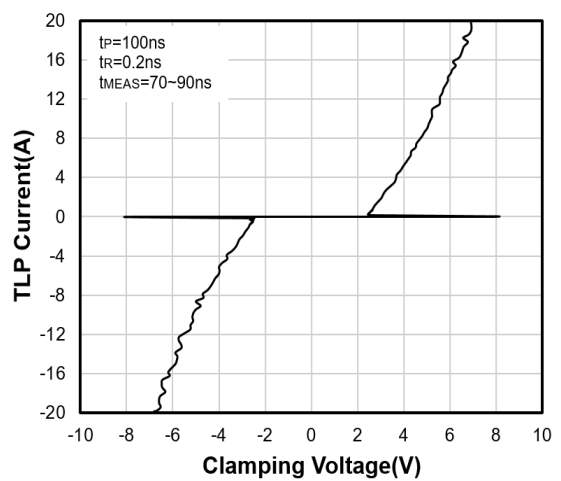
Junction Capacitance vs. Reverse Voltage



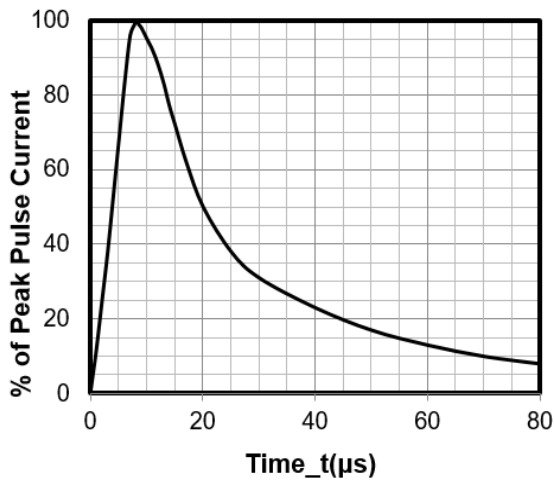
Peak Pulse Power vs. Pulse Time



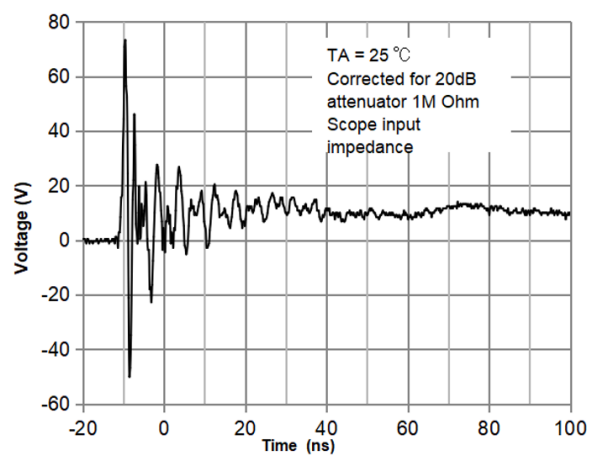
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



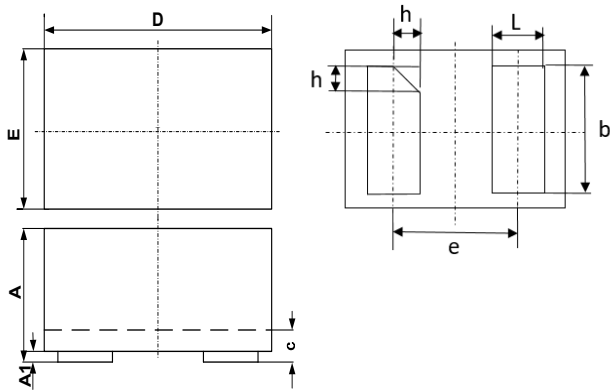
8 X 20μs Pulse Waveform



ESD Clamping Voltage

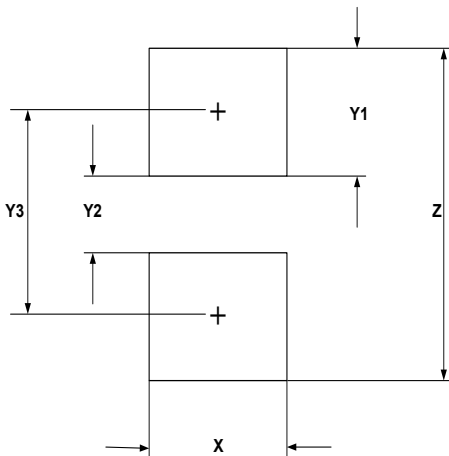
8 kV Contact per IEC61000-4-2

DFN0603-2 Package Outline Drawing



SYM	DIMENSIONS		
	MILLIMETERS		
	MIN	NOM	MAX
A	0.230	--	0.330
A1	0.000	0.020	0.050
b	0.215	0.245	0.275
c	0.120	0.150	0.180
D	0.550	0.600	0.650
e	0.355 BSC		
E	0.250	0.300	0.350
L	0.160	0.190	0.220
h	0.079 BSC		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.30	0.012
Y1	0.25	0.010
Y2	0.15	0.006
Y3	0.40	0.016
Z	0.65	0.026

Contact Information

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